

Bias Resistor Transistor

PNP Silicon Surface Mount Transistor with Monolithic Bias Resistor Network

LDTA114WET1G

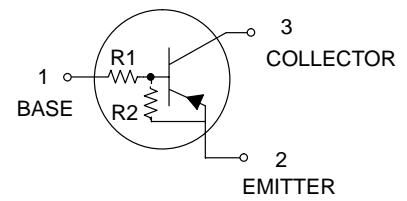
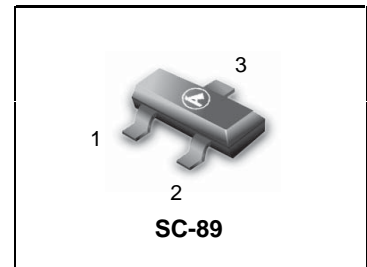
● **Applications**

Inverter, Interface, Driver

● **Features**

- 1) Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- 2) The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- 3) Only the on / off conditions need to be set for operation, making the device design easy.
- 4) Higher mounting densities can be achieved.

- We declare that the material of product compliance with RoHS requirements.



● **Absolute maximum ratings** (Ta=25°C)

Parameter	Symbol	Limits	Unit
Supply voltage	V _{CC}	-50	V
Input voltage	V _I	-30 to +10	V
Output current	I _O	-100	mA
	I _{C(Max.)}	-100	
Power dissipation	P _D	200	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

DEVICE MARKING AND RESISTOR VALUES

Device	Marking	R1 (K)	R2 (K)	Shipping
LDTA114WET1G	L6	10	4.7	3000/Tape & Reel
LDTA114WET3G	L6	10	4.7	10000/Tape & Reel

● **External characteristics** (Unit: mm)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	V _{I(off)}	-	-	-0.8	V	V _{CC} =-5V, I _O =-100μA
	V _{I(on)}	-3	-	-		V _O =-0.3V, I _O =-2mA
Output voltage	V _{O(on)}	-	-0.1	-0.3	V	I _O =-10mA, I _I =-0.5mA
Input current	I _I	-	-	-0.88	mA	V _I =-5V
Output current	I _{O(off)}	-	-	-0.5	μA	V _{CC} =-50V, V _I =0V
DC current gain	G _I	24	-	-	-	I _O =-10mA, V _O =-5V
Input resistance	R _I	7	10	13	kΩ	-
Resistance ratio	R ₂ /R ₁	0.37	0.47	0.57	-	-
Transition frequency	f _T *	-	250	-	MHz	V _{CE} =-10V, I _E =5mA, f=100MHz

* Characteristics of built-in transistor

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● **Electrical characteristics curves**

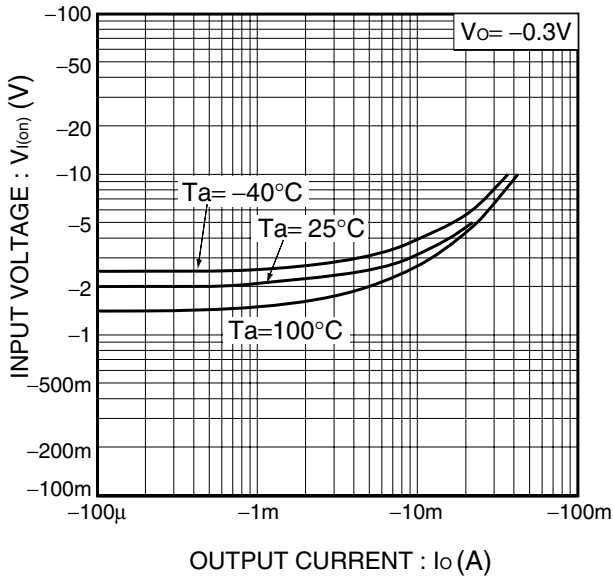


Fig.1 Input voltage vs. Output current (ON characteristics)

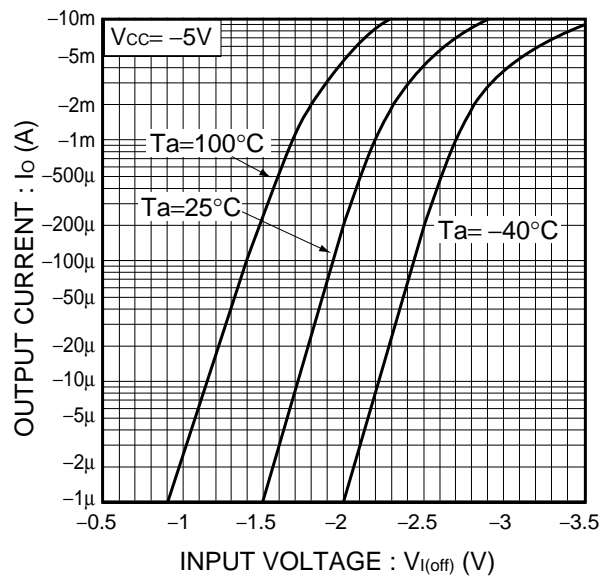


Fig.2 Output current vs. Input voltage (OFF characteristics)

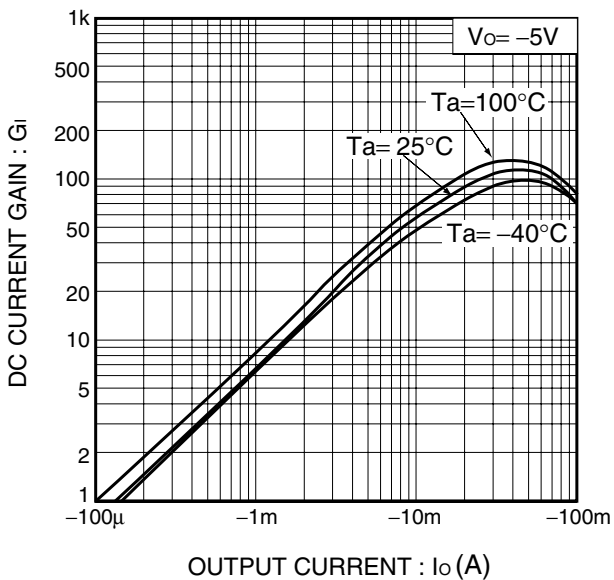


Fig.3 DC current gain vs. Output current

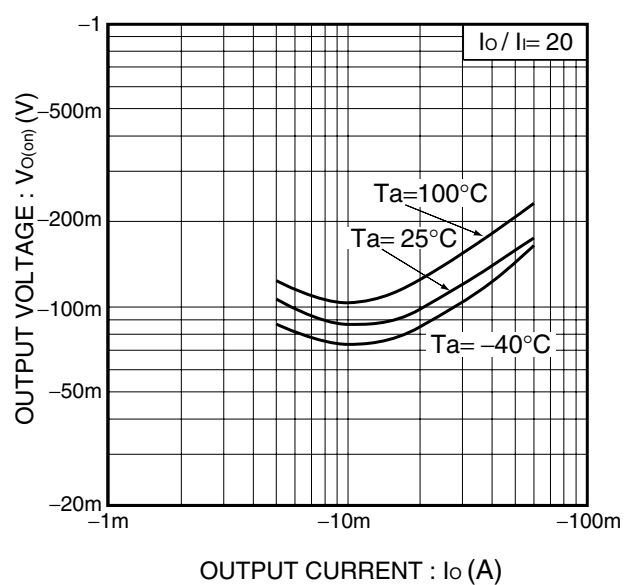
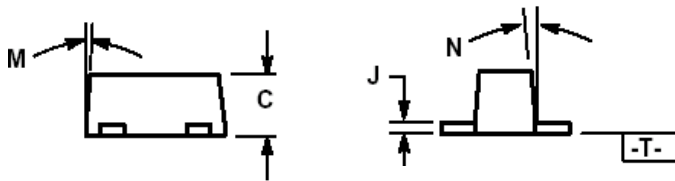


Fig.4 Output voltage vs. Output current

LDTA114WET1G
SC-89

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS
3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
4. 463C-01 OBSOLETE, NEW STANDARD 463C-02.



DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.60	1.70	0.059	0.063	0.067
B	0.75	0.85	0.95	0.030	0.034	0.040
C	0.60	0.70	0.80	0.024	0.028	0.031
D	0.23	0.28	0.33	0.009	0.011	0.013
G	0.50 BSC			0.020 BSC		
H	0.53 REF			0.021 REF		
J	0.10	0.15	0.20	0.004	0.006	0.008
K	0.30	0.40	0.50	0.012	0.016	0.020
L	1.10 REF			0.043 REF		
M	---	---	10 °	---	---	10 °
N	---	---	10 °	---	---	10 °
S	1.50	1.60	1.70	0.059	0.063	0.067

